1SS315

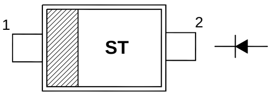
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

- UHF Band Mixer

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



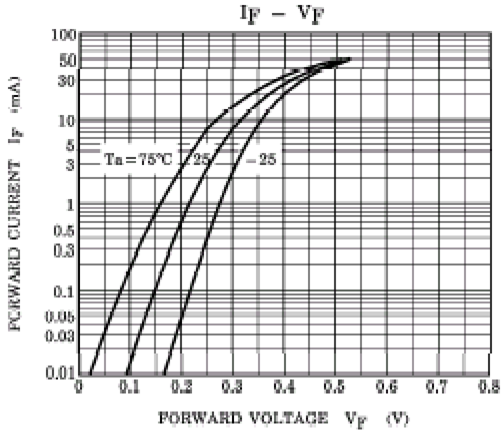
Top View
Marking Code: "**ST**"
Simplified outline SOD-323 and symbol

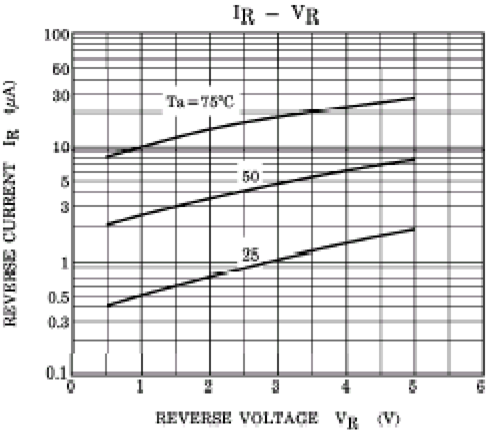
Absolute Maximum Ratings (T_a = 25 °C)

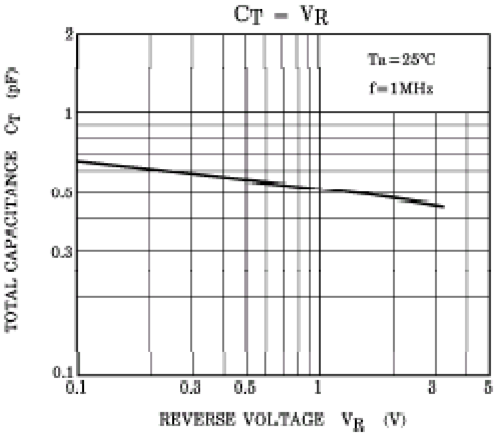
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	5	V
Forward Current	I_F	30	mA
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

Electrical Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Current at V_F = 0.5 V	I_F	30	-	-	mA
Reverse Current at V_R = 0.5 V	I_R	-	-	25	µA
Total Capacitance at V_R = 0.2 V, f = 1 MHz	C_T	-	0.6	-	pF

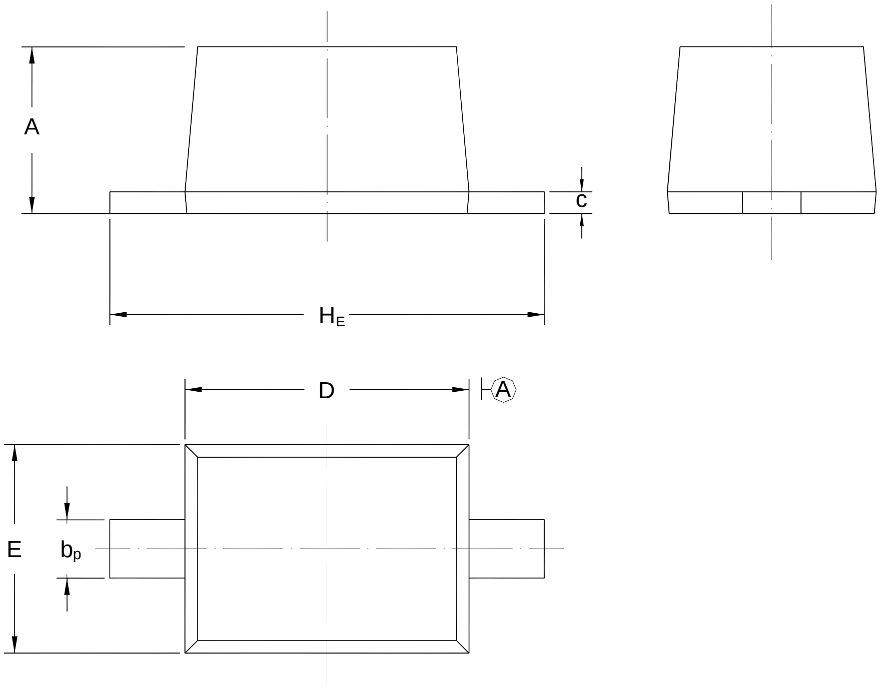

IF – VF
FORWARD CURRENT IF (mA)
100
50
30
10
5
3
1
0.5
0.3
0.1
0.05
0.03
0.01
Ta = 75°C
25
– 25
0
0.1
0.2
0.3
0.4
0.5
0.6
0.7
0.8
FORWARD VOLTAGE VF (V)


IR – VR
REVERSE CURRENT IR (μA)
100
50
30
10
5
3
1
0.5
0.3
0.1
Ta = 75°C
50
25
0
1
2
3
4
5
6
REVERSE VOLTAGE VR (V)


CT – VR
TOTAL CAPACITANCE CT (pF)
2
1
0.5
0.3
0.1
Ta = 25°C
f = 1MHz
0.1
0.3
0.5
1
3
5
REVERSE VOLTAGE VR (V)

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-323**



UNIT	A	b_p	C	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30